

Supporting Information

Plasma-enhanced low-temperature ALD process for molybdenum oxide thin films and its evaluation as hydrogen gas sensors

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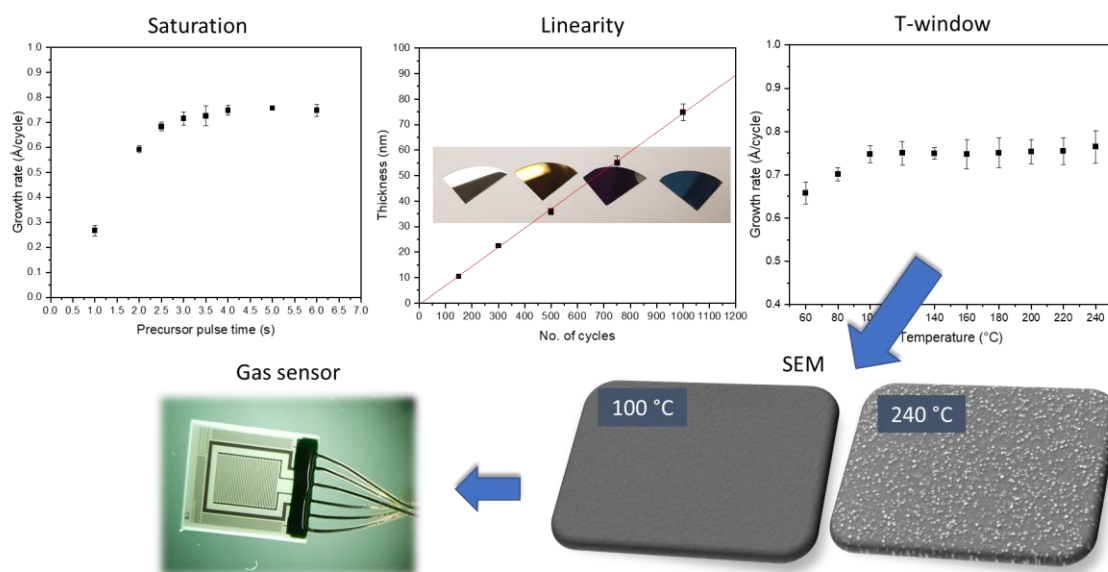


Figure 1. Characteristics of the PEALD process. Morphology of the resulting thin films and utilized sensor chips for resistive hydrogen gas sensing.

References

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